L Number	Hits	Search Text	DB	Time stamp
-	69	breakdown adj phenom\$4 NEAR5 dielectric	USPAT;	2004/03/02 13:55
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	1	"breakdown phenomena" near5 "ultra-thin dielectric layer"	USPAT;	2004/03/02 11:14
		,	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	214	"breakdown phenomena"	USPAT;	2004/03/02 14:36
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	54	"ultra-thin dielectric layer"	USPAT;	2004/03/02 14:41
	•	,	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	12	"breakdown phenomena" and " memory device"	USPAT;	2004/03/02 11:14
	12	2. Canadani prioritatia ana monory device	US-PGPUB;	
	!		EPO; JPO;	
			DERWENT	
_	4	(("6671040") or ("6667902")).PN.	USPAT:	2004/03/02 11:14
-	4	((001 1040) 01 (0001902)).FN.	US-PGPUB;	
1			EPO: JPO:	
			DERWENT	
	14	BREAKDOWN ADJ PHENOMENA ADJ ULTRA-THIN ADJ	USPAT;	2004/03/02 11:14
-	14	DIELECTRIC	US-PGPUB;	2004/03/02 11.14
		DIELECTRIC	EPO; JPO;	
			DERWENT	
	2	20020062549		2004/02/02 11:14
-	2	"20030063518"	USPAT;	2004/03/02 11:14
			US-PGPUB;	
			EPO; JPO; DERWENT	
	60	(headedown or (headele adid down)) adi phonomed NEADE		2004/03/02 11:14
-	69	(breakdown or (breask adj1 down)) adj phenom\$4 NEAR5	USPAT; US-PGPUB;	2004/03/02 11:14
		dielectric		
			EPO; JPO; DERWENT	
	-	"breakdown phenomena" and "ultra-thin dielectric layer"	USPAT;	2004/03/02 11:59
-	. 7	breakdown phenomena and ultra-thin dielectric layer	US-PGPUB;	2004/03/02 11.59
			EPO; JPO;	
	0	(IIC700454II) PN	DERWENT	2004/02/02 44:44
-	2	("6700151").PN.	USPAT;	2004/03/02 11:14
			US-PGPUB;	
	!		EPO; JPO;	
	^	"ultre this diplostric lover" and breakdown adi where	DERWENT	2004/03/02 11:14
-	9	"ultra-thin dielectric layer" and breakdown adj phenom\$9	USPAT;	2004/03/02 11:14
			US-PGPUB;	
1			EPO; JPO; DERWENT	
	4	"brookdown phonomono" and "somiconductor more		2004/02/02 11:14
-	4	"breakdown phenomena" and "semiconductor memory	USPAT;	2004/03/02 11:14
		device"	US-PGPUB;	
			EPO; JPO;	
	,	Bullium Albim Mining Admin Journally and Burnayan and Assistants	DERWENT	2004/02/02 44:44
-	1	"ultra-thin dielectric layer" and " memory device"	USPAT;	2004/03/02 11:14
			US-PGPUB;	
			EPO; JPO;	
	4	(/ICO74040II) /ICCC7000II) DAI	DERWENT	0004/00/00 11 11
-	4	(("6671040") or ("6667902")).PN.	USPAT;	2004/03/02 11:14
			US-PGPUB;	
			EPO; JPO;	
	_		DERWENT	0004/00/00 11 77
] -	2	"20040008538"	USPAT;	2004/03/02 11:59
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	

	2	("6215140").PN.	USPAT;	2004/03/02 14:10
1 -	-	(02 13 170).CN.	US-PGPUB;	2007/00/02 17.10
			EPO; JPO;	
			DERWENT	
	2	("4037243").PN.	USPAT:	2004/03/02 14:34
-	2	(403/243 J.FN.	US-PGPUB;	2004/03/02 14.54
			EPO; JPO;	
			DERWENT	
	31986	programmable adit road aditanty adit mamany	USPAT;	2004/03/02 14:40
-	31900	programmable adj1 read adj1only adj1 memory	US-PGPUB;	2004/03/02 14.40
			EPO; JPO;	
			DERWENT	
	00055			2004/02/02 44:26
-	20955	programmable adj1 read adj1only adj1 memory	USPAT	2004/03/02 14:36
-	9	(programmable adj1 read adj1only adj1 memory) and	USPAT;	2004/03/02 14:52
		"breakdown phenomena"	US-PGPUB;	
			EPO; JPO;	
			DERWENT	0004/00/00 44 45
-	31557	"programmable read only memory"	USPAT;	2004/03/02 14:40
	1		US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	20695	"programmable read only memory"	USPAT	2004/03/02 14:41
-	3	"programmable read only memory" and "ultra-thin dielectric	USPAT;	2004/03/02 14:41
		layer"	US-PGPUB;	
	ŧ		EPO; JPO;	
			DERWENT	
-	2	"20030071296"	USPAT;	2004/03/02 14:52
			US-PGPUB;	
			EPO; JPO;	
		·	DERWENT	
_	4	"20030071296" or "20030071315"	USPAT;	2004/03/02 15:34
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	2	("6700151").PN.	USPAT;	2004/03/02 15:34
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	6	("20030071296" or "20030071315") or (("6700151").PN.)	USPAT;	2004/05/03 06:37
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	3	("6700151").PN.	USPAT;	2004/05/03 07:38
		,	US-PGPUB;	
			EPO; JPO;	
			DERWENT	